

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	<110> +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none / Semi Standard	
	5.0	Secondary Flat Length	none	Wafer Vendor
	6.0	Overall Thickness	331.00 +/- 12.00 µm	ADE 100%
	7.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	8.0	Bow	<60.00µm	ADE to ASTM F534, 20%
	9.0	Warp	<60.00µm	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	14.0	Handle Thickness	300.00 +/- 10.00 µm	ADE, 100%
	15.0	Handle Doping Type	P	Wafer Vendor
	16.0	Handle Dopant	Boron	Wafer Vendor
	17.0	Handle Resistivity	0.01- 0.02 Ohmcm	Wafer Vendor
	19.0	Backside Finish	Polished with oxide and lasermark	Wafer Vendor
	BuriedOxide	20.0	Oxide Type	Thermal
21.0		Oxide Thickness	10,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
22.0		Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	23.0	Device Growth Method	CZ	Wafer Vendor
	24.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	25.0	Nominal Thickness	30.00 +/- 1.00 µm	FTIR, 100% 9-Pt (note3)
	26.0	Distance to device silicon edge from wafer edge	< 2 mm	Guaranteed by Process
	27.0	Device Doping Type	P	Wafer Vendor
	28.0	Device Dopant	Boron	Wafer Vendor
	29.0	Device Resistivity	0.01- 0.02 Ohmcm	Wafer Vendor
	31.0	Voids	0	Bright Light, 100% (note 2)
	32.0	Scratches	0	Bright Light, 100% (note 2)
	33.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer
-------------	----------

Category	Parameter	Specification	Measurement Method
----------	-----------	---------------	--------------------

Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information